Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
-60V	250mΩ @ V_{GS} = -10V	-6.1A
	300mΩ @ V_{GS} = -4.5V	-5.6A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low Gate Drive
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMP6250SEQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

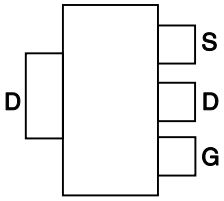
- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Mechanical Data

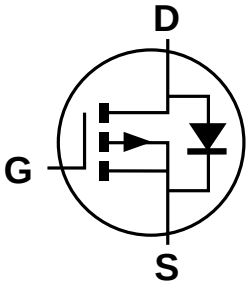
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.112 grams (Approximate)

SOT223

Top View



Pin Out - Top View



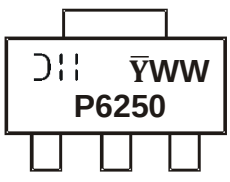
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP6250SEQ-13	SOT223	2,500 / Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
P6250 = Marking Code
$\overline{Y}$WW = Date Code Marking
$\overline{Y}$ = Year (ex: 0 = 2020)
WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = -10V	T_C = +25°C T_C = +70°C	I_D	-6.1 -4.9	A
Maximum Body Diode Continuous Current		I_S	-6.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	-14	A
Single Pulsed Avalanche Current (Note 6) L = 0.1mH		I_{AS}	-12	A
Single Pulsed Avalanche Energy (Note 6) L = 0.1mH		E_{AS}	8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	1.8	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	69	°C/W
Total Power Dissipation (Note 5)	T_C = +25°C	P_D	14	W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	8.7	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	I_D = -250µA, V_{GS} = 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	µA	V_{DS} = -60V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-3	V	V_{DS}= V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	128	250	mΩ	V_{GS} = -10V, I_D = -1.0A
			156	300		V_{GS} = -4.5V, I_D = -0.5A
Diode Forward Voltage	V_{SD}	—	-0.8	-1.2	V	V_{GS} = 0V, I_S = -2.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	551	—	pF	V_{DS} = -30V, V_{GS} = 0V f= 1MHz
Output Capacitance	C_{oss}	—	25.7	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	19.1	—	pF	
Gate Resistance	R_g	—	12.1	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	4.8	—	nC	V_{DS} = -30V, I_D = -2A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	9.7	—	nC	
Gate-Source Charge	Q_{gs}	—	1.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.6	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	6.3	—	ns	V_{DS} = -30V, V_{GS} = -10V, R_G = 50Ω, I_D = -1A
Turn-On Rise Time	t_R	—	10.3	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	91.4	—	ns	
Turn-Off Fall Time	t_F	—	39.8	—	ns	
Reverse Recovery Time	t_{RR}	—	9.2	—	ns	I_S = -1A, di/dt= 100A/µs
Reverse Recovery Charge	Q_{RR}	—	3.9	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
7. Short duration pulse test used to minimize self-heating effect.
8. For design aid only, not subject to production testing.

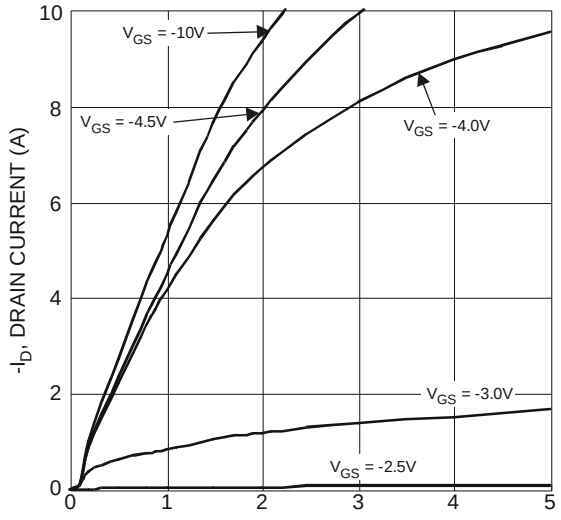


Figure 1 Typical Output Characteristics

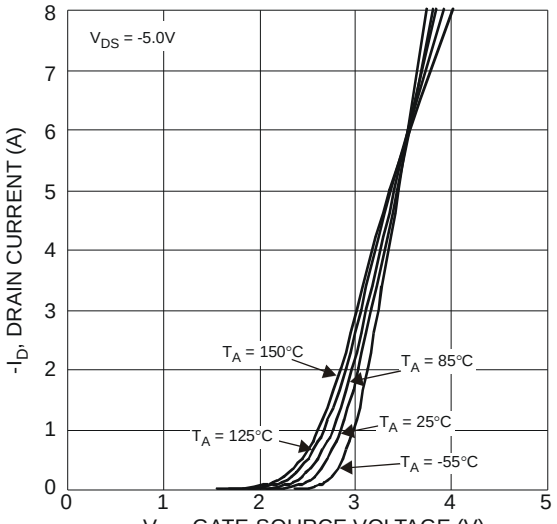


Figure 2 Typical Transfer Characteristics

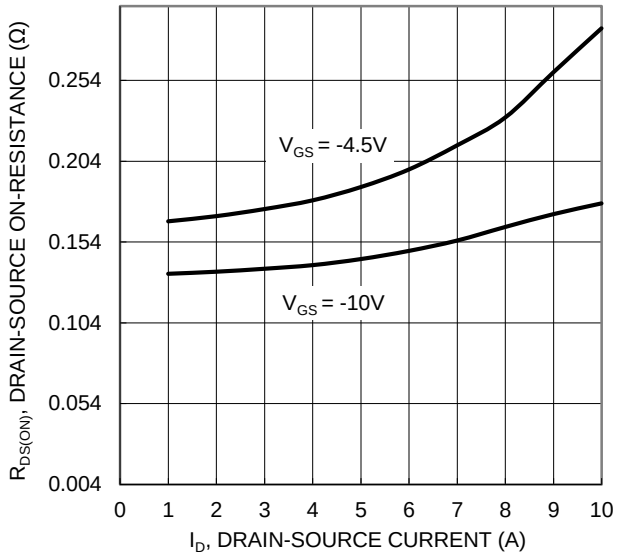


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

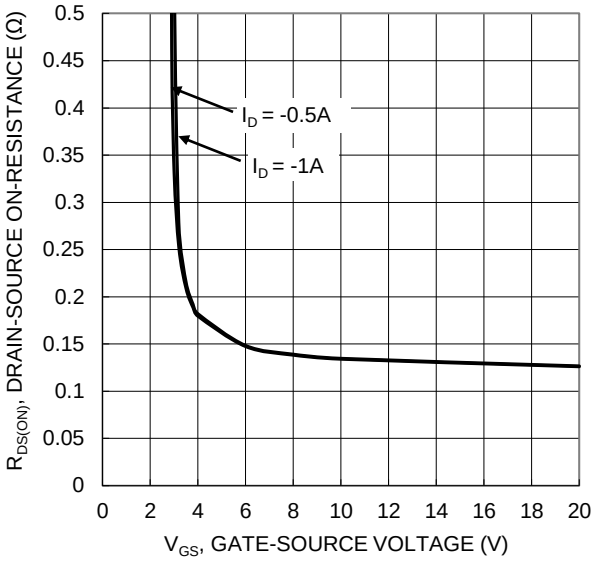


Figure 4. Typical Transfer Characteristic

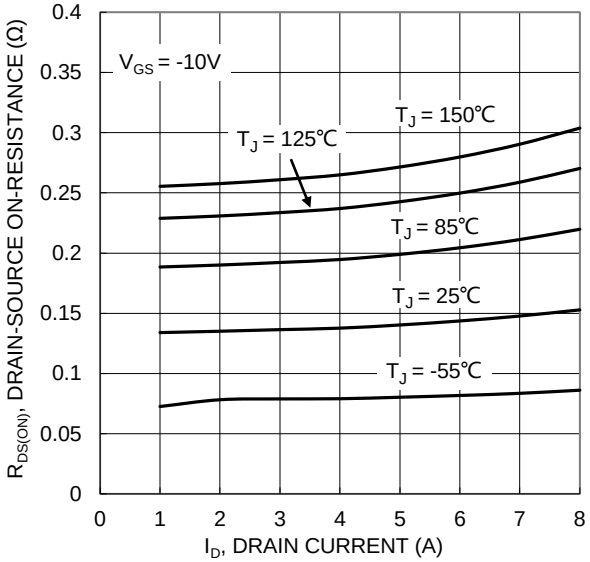


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

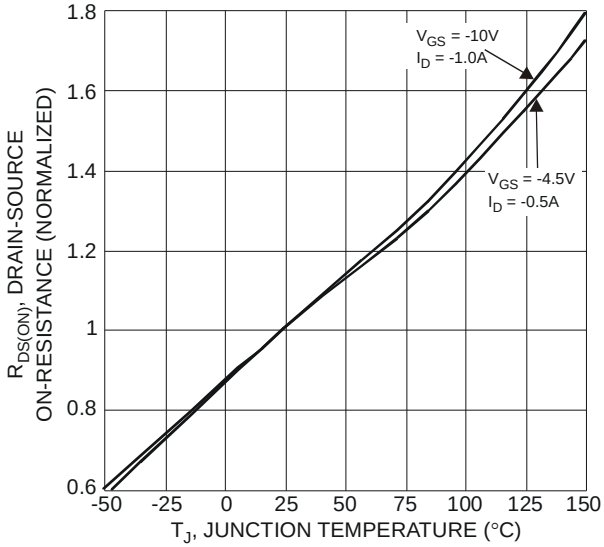


Figure 6 On-Resistance Variation with Temperature

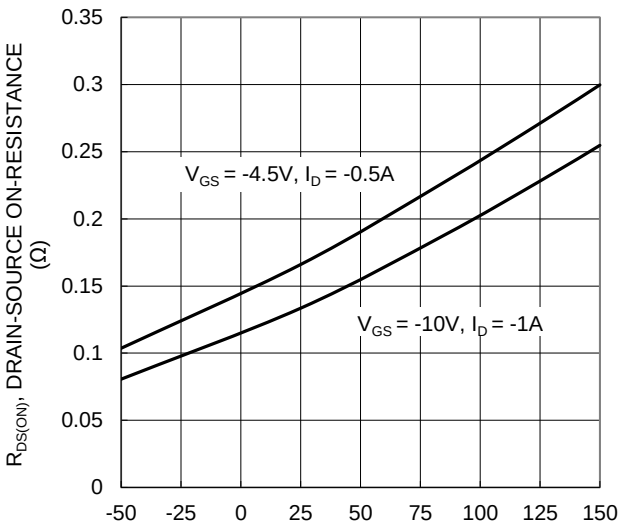


Figure 7. On-Resistance Variation with Temperature

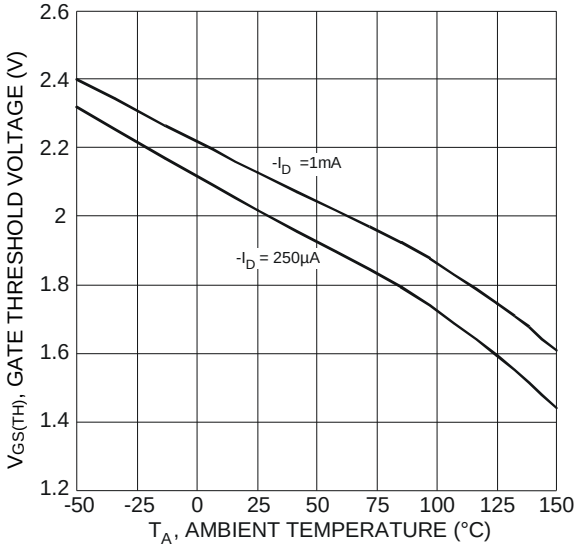


Figure 8 Gate Threshold Variation vs. Ambient Temperature

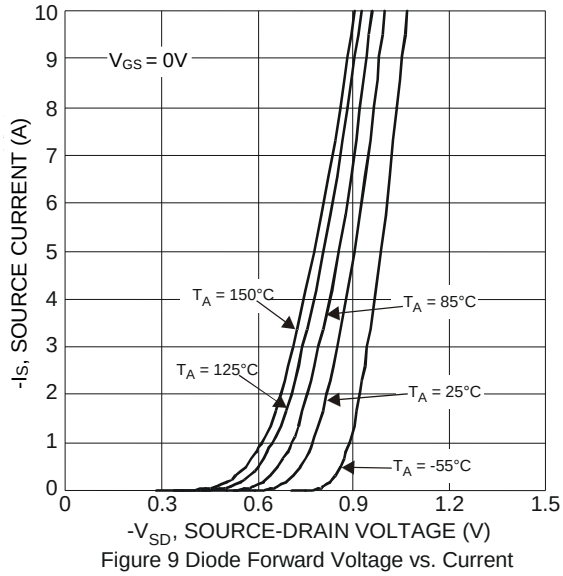


Figure 9 Diode Forward Voltage vs. Current

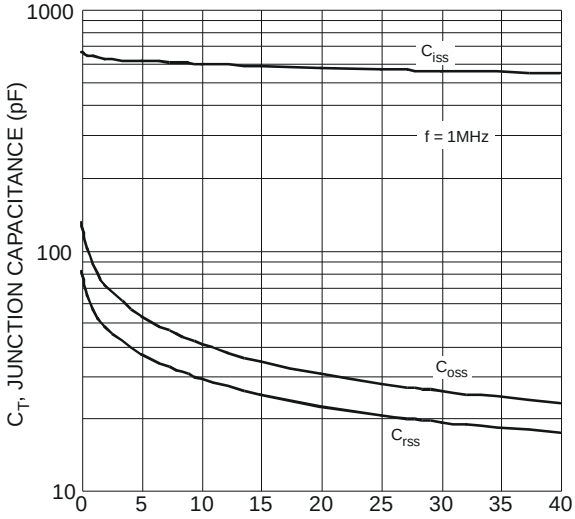


Figure 10 Typical Junction Capacitance

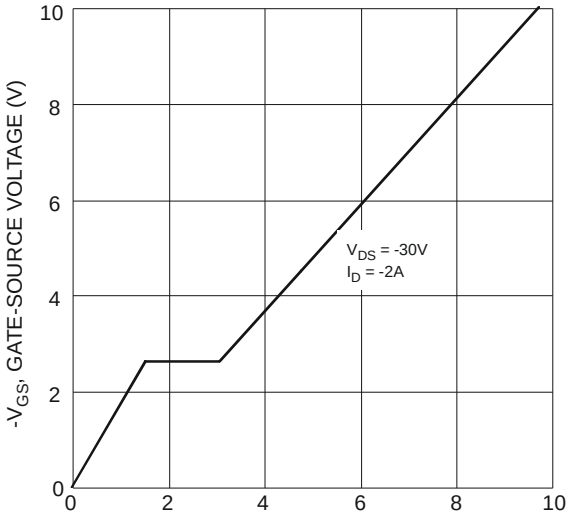


Figure 11 Gate-Charge Characteristics

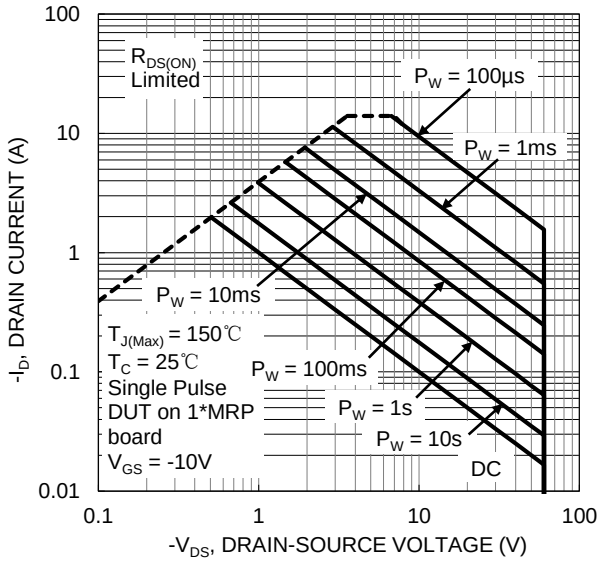


Figure 12. SOA, Safe Operation Area

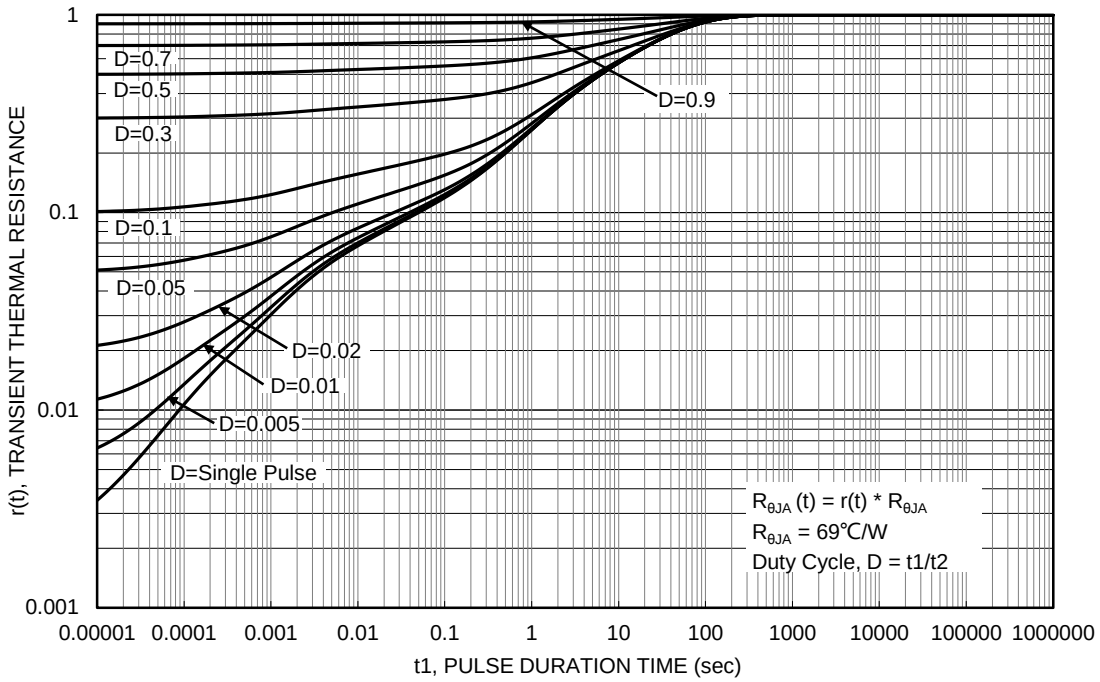
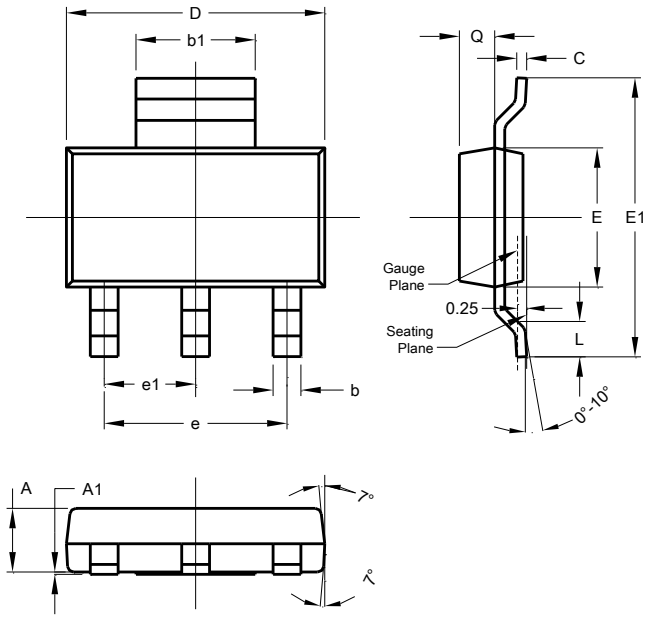


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223

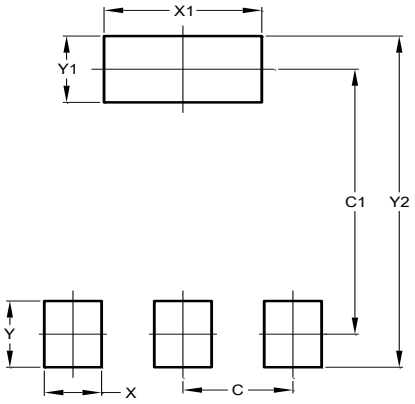


SOT223			
Dim	**Min**	**Max**	**Typ**
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00

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